

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-16V	18mΩ@-4.5V	-6A
	20mΩ@-3.7V	
	26mΩ@-2.5V	
	38mΩ@-1.8V	
	56mΩ@-1.5V	

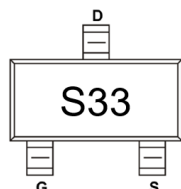
Feature

- Trench Technology Power MOSFET
- Low $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance

Application

- DC/DC Converter
- Load Switch for Portable Devices
- Battery Switch

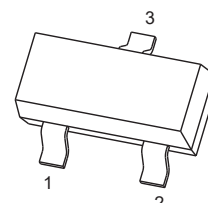
MARKING



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

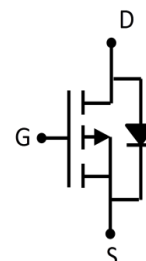
Parameter	Symbol	Value	Unit
Drain - Source Voltage	V_{DS}	-16	V
Gate - Source Voltage	V_{GS}	±10	V
Continuous Drain Current ¹	I_D	-6	A
Pulsed Drain Current ²	I_{DM}	-20	A
Power Dissipation ⁵	P_D	0.35	W
Thermal Resistance from Junction to Ambient ⁶	$R_{\theta JA}$	357	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^\circ\text{C}$

SOT-23



1. GATE
2. SOURCE
3. DRAIN

Schematic diagram



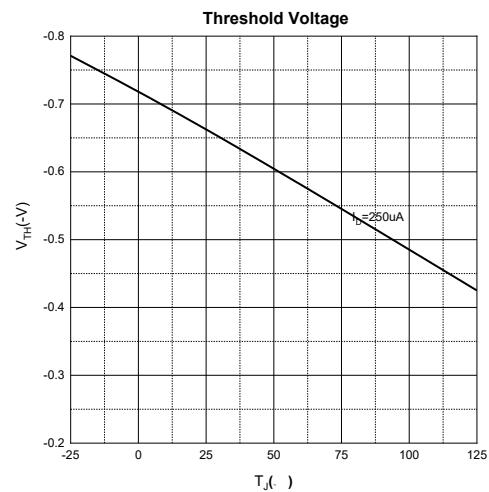
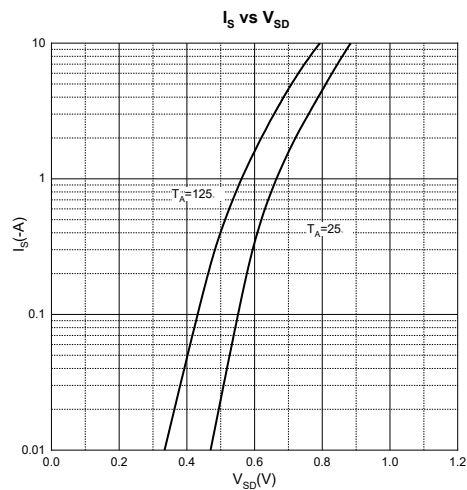
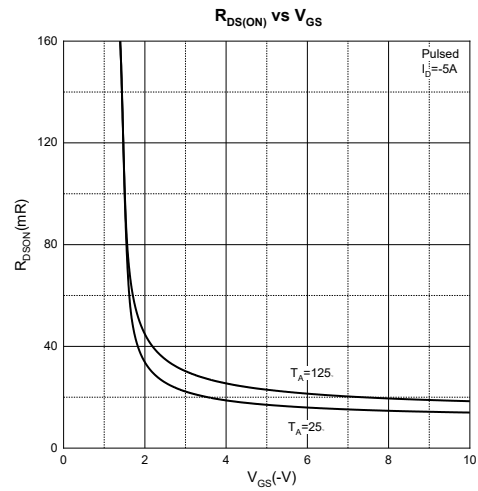
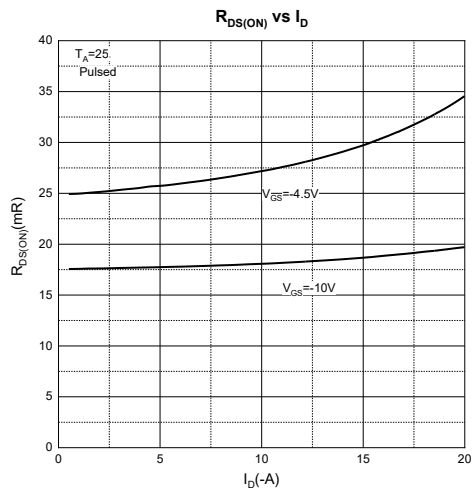
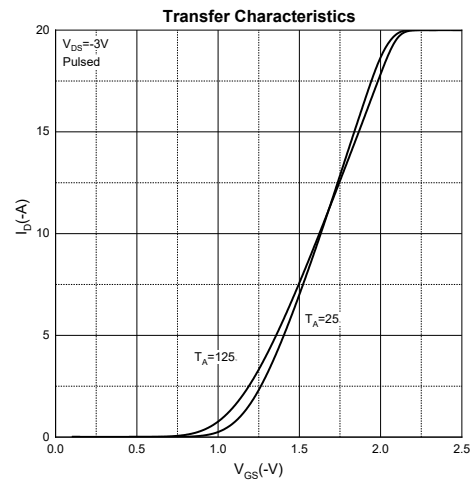
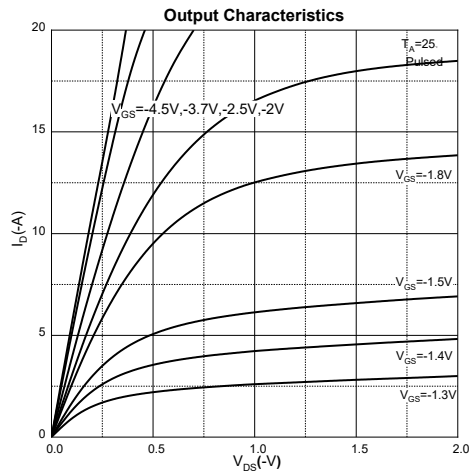
MOSFET ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

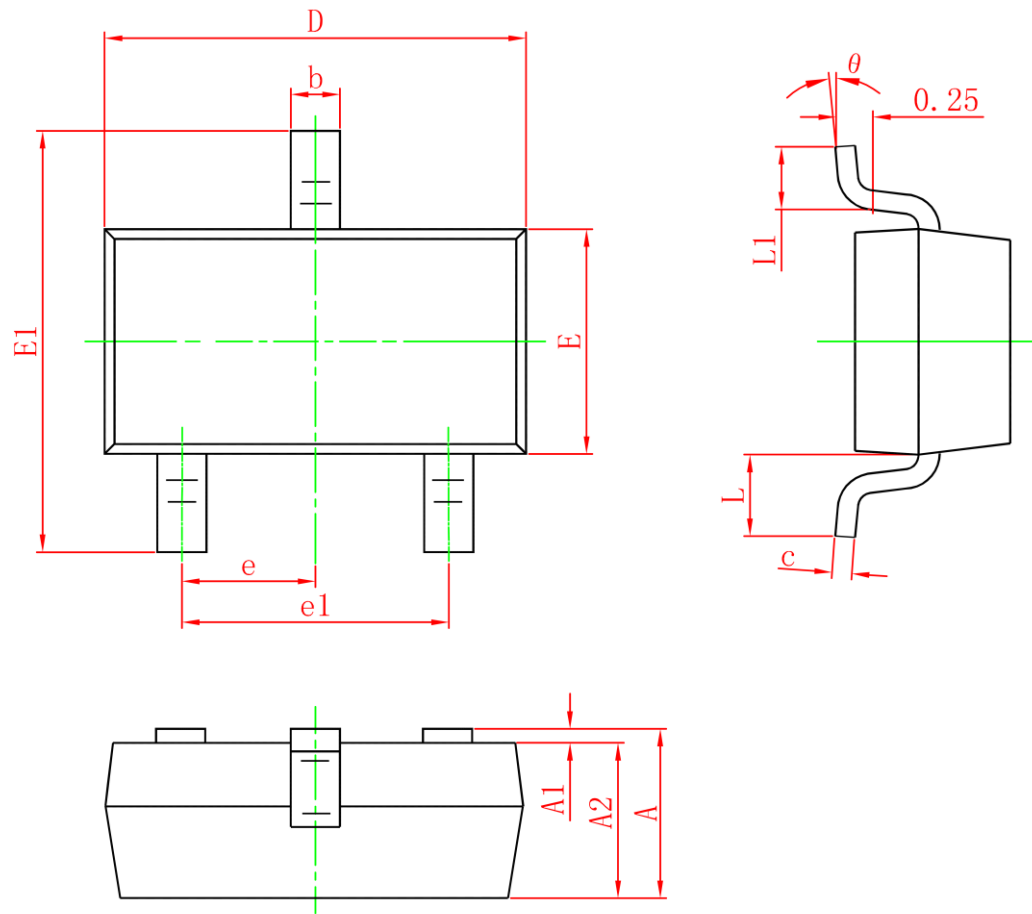
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-16			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -12V, V_{GS} = 0V$			1	μA
Gate - Body Leakage Current	I_{GSS}	$V_{GS} = \pm 10V, V_{DS} = 0V$			± 100	nA
On Characteristics ⁴						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.4	-0.7	-1.0	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -5.0A$		18	28	m Ω
		$V_{GS} = -3.7V, I_D = -4.6A$		20	32	
		$V_{GS} = -2.5V, I_D = -4.3A$		26	40	
		$V_{GS} = -1.8V, I_D = -1.0A$		38	63	
		$V_{GS} = -1.5V, I_D = -0.5A$		56	150	
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = -8V, V_{GS} = 0V, f = 1MHz$		640		pF
Output Capacitance	C_{oss}			152		
Reverse Transfer Capacitance	C_{rss}			143		
Gate Resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		6.2		Ω
Switching Characteristics						
Total Gate Charge	Q_g	$V_{DS} = -4.5V, V_{GS} = -10V, I_D = -5A$		9.5		nC
Gate-source Charge	Q_{gs}			1.0		
Gate-drain Charge	Q_{gd}			3.3		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = -6V, V_{GS} = -4.5V, I_D = -4A, R_G = 1\Omega$		26		ns
Turn-on Rise Time	t_r			24		
Turn-off Delay Time	$t_{d(off)}$			45		
Turn-off Fall Time	t_f			20		
Source - Drain Diode Characteristics						
Diode Forward Voltage ⁴	V_{SD}	$V_{GS} = 0V, I_S = -4A$			-1.2	V

Notes :

- 1.The maximum current rating is limited by package.And device mounted on a large heatsink
- 2.Pulse Test : Pulse Width $\leq 10\mu s$, duty cycle $\leq 1\%$.
- 3.Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 4.The power dissipation P_D is limited by $T_{J(MAX)} = 150^\circ\text{C}$.And device mounted on a large heatsink
- 5.Device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

Typical Characteristics



SOT-23 Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0	0.100	0	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.150	1.500	0.045	0.059
E1	2.250	2.650	0.089	0.104
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

Attention:

- GreenPower Electronics reserves the right to improve product design function and reliability without notice.
- Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.
- GreenPower Electronics products belong to consumer electronics or other civilian electronic products.